

FIG. 1

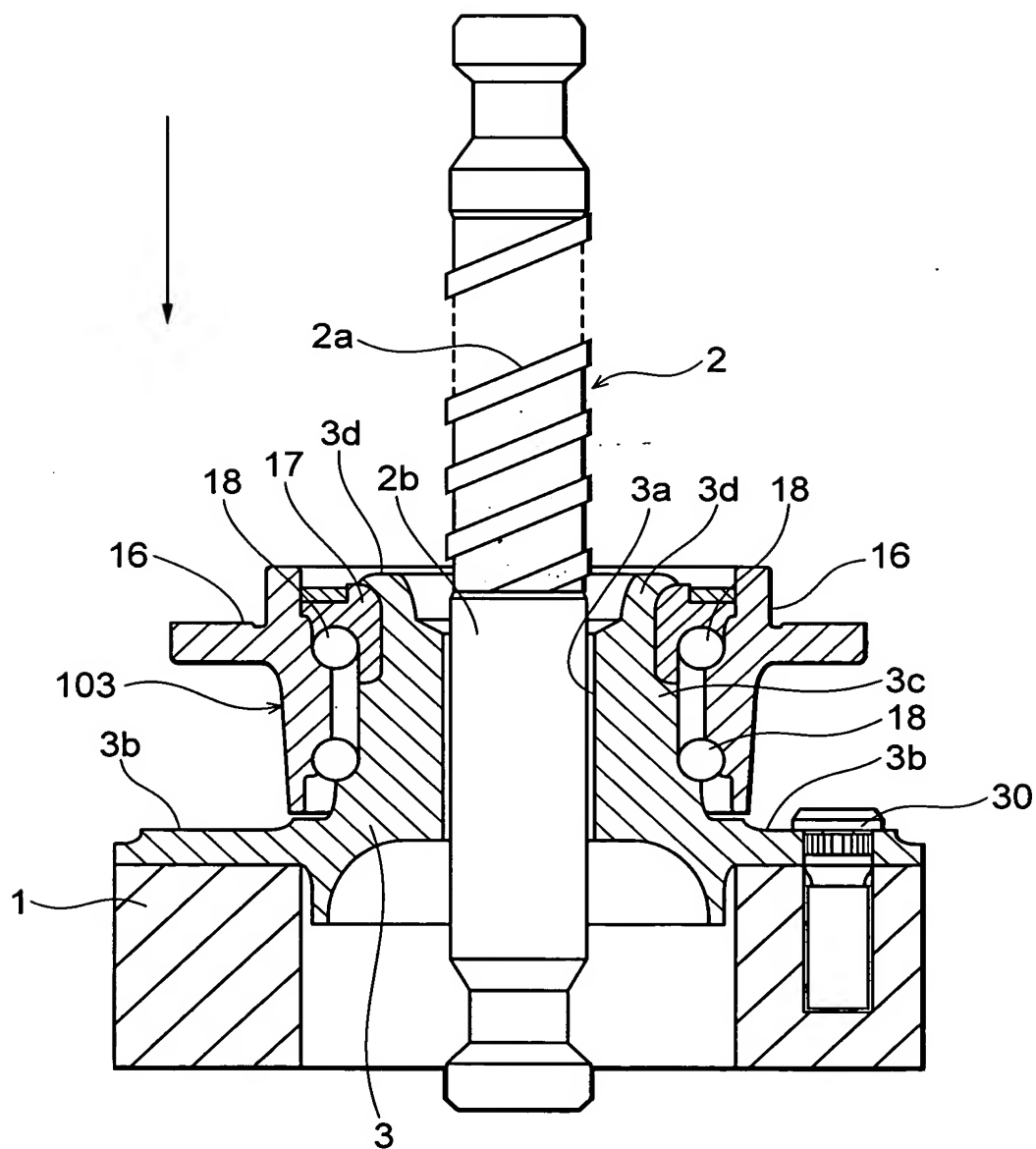


FIG. 3A

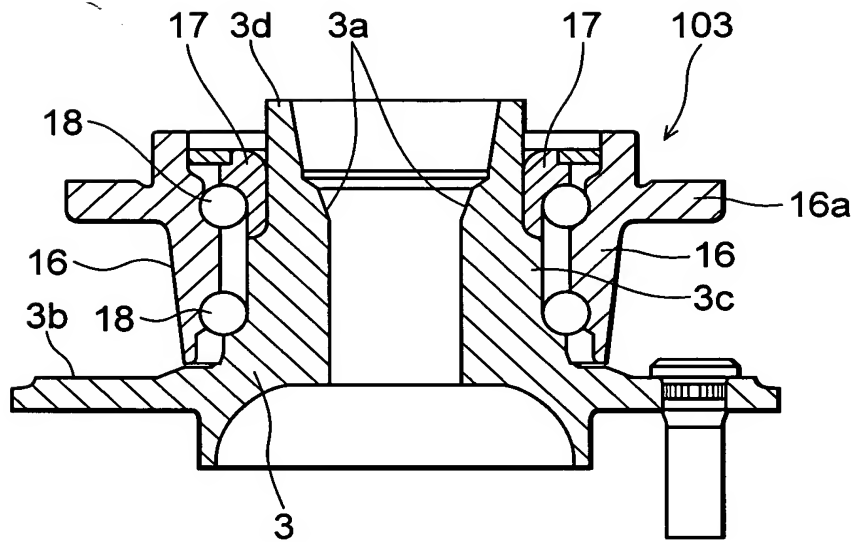


FIG. 3B

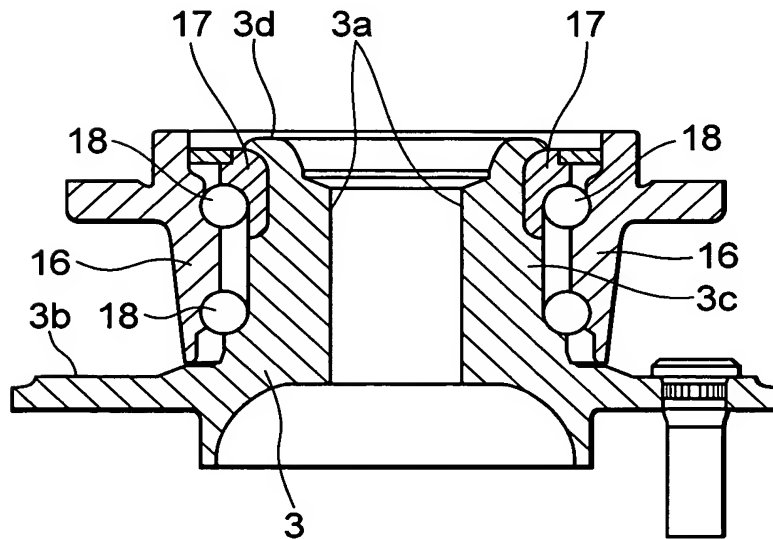


FIG. 4A

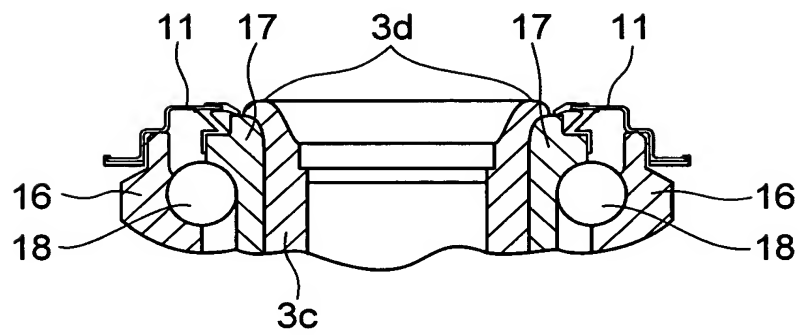


FIG. 4B

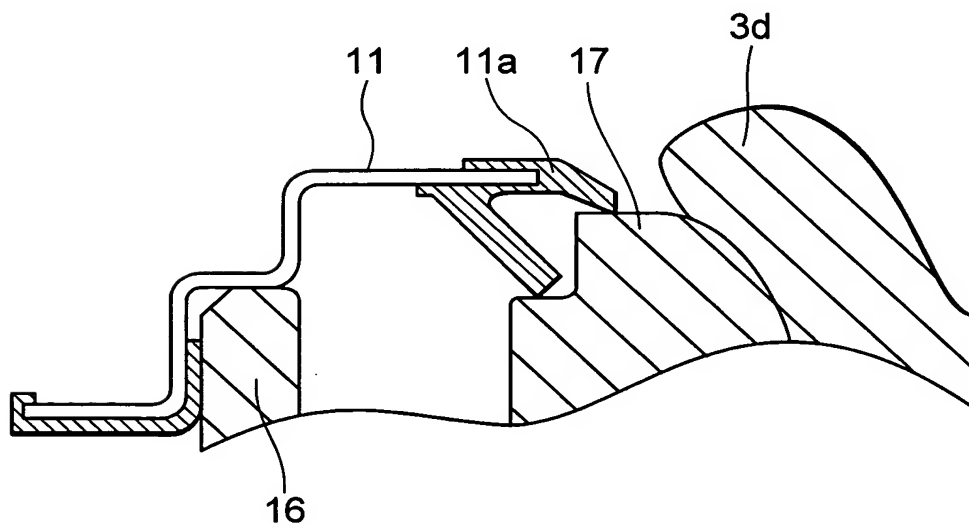


FIG. 5

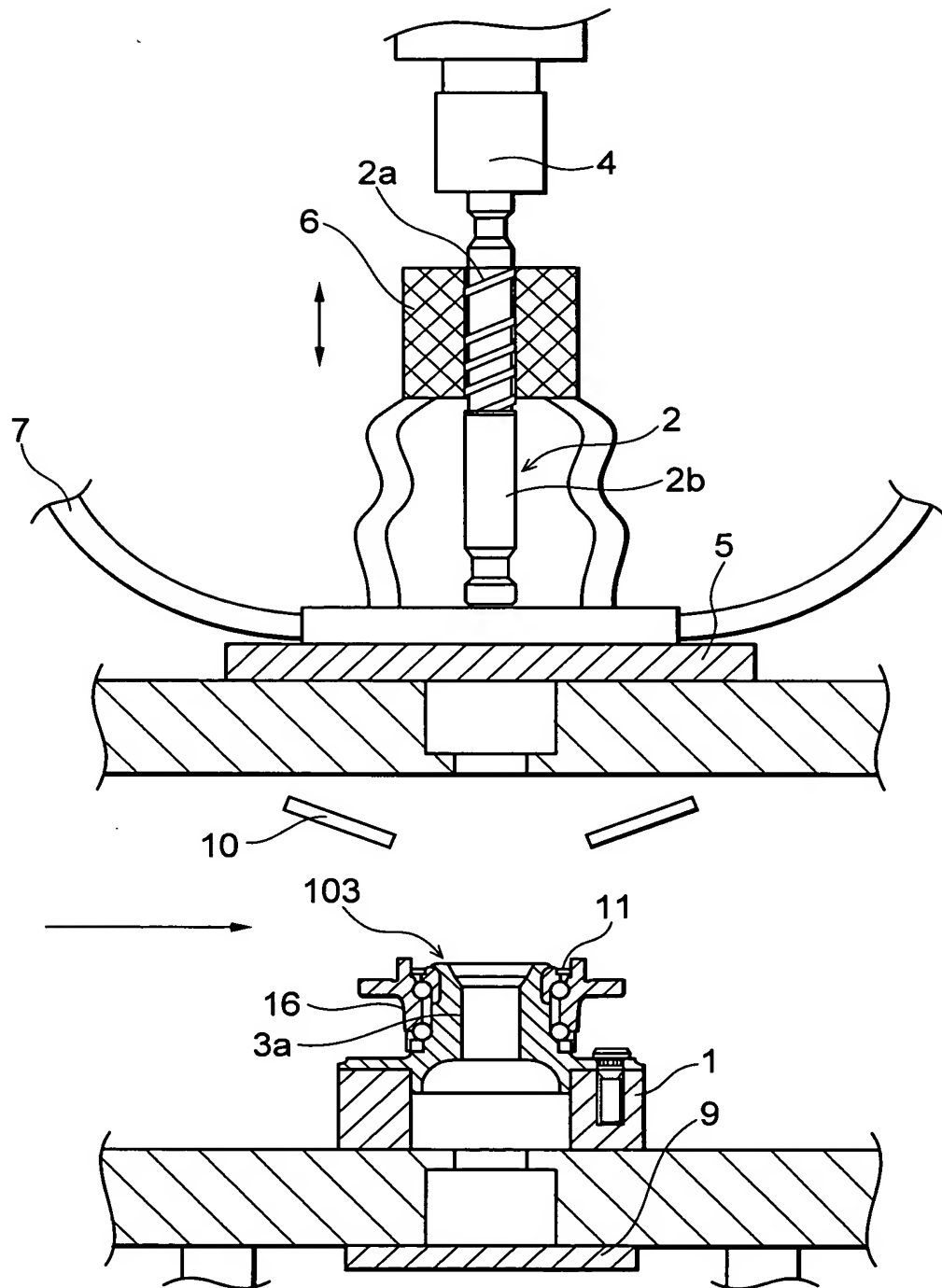
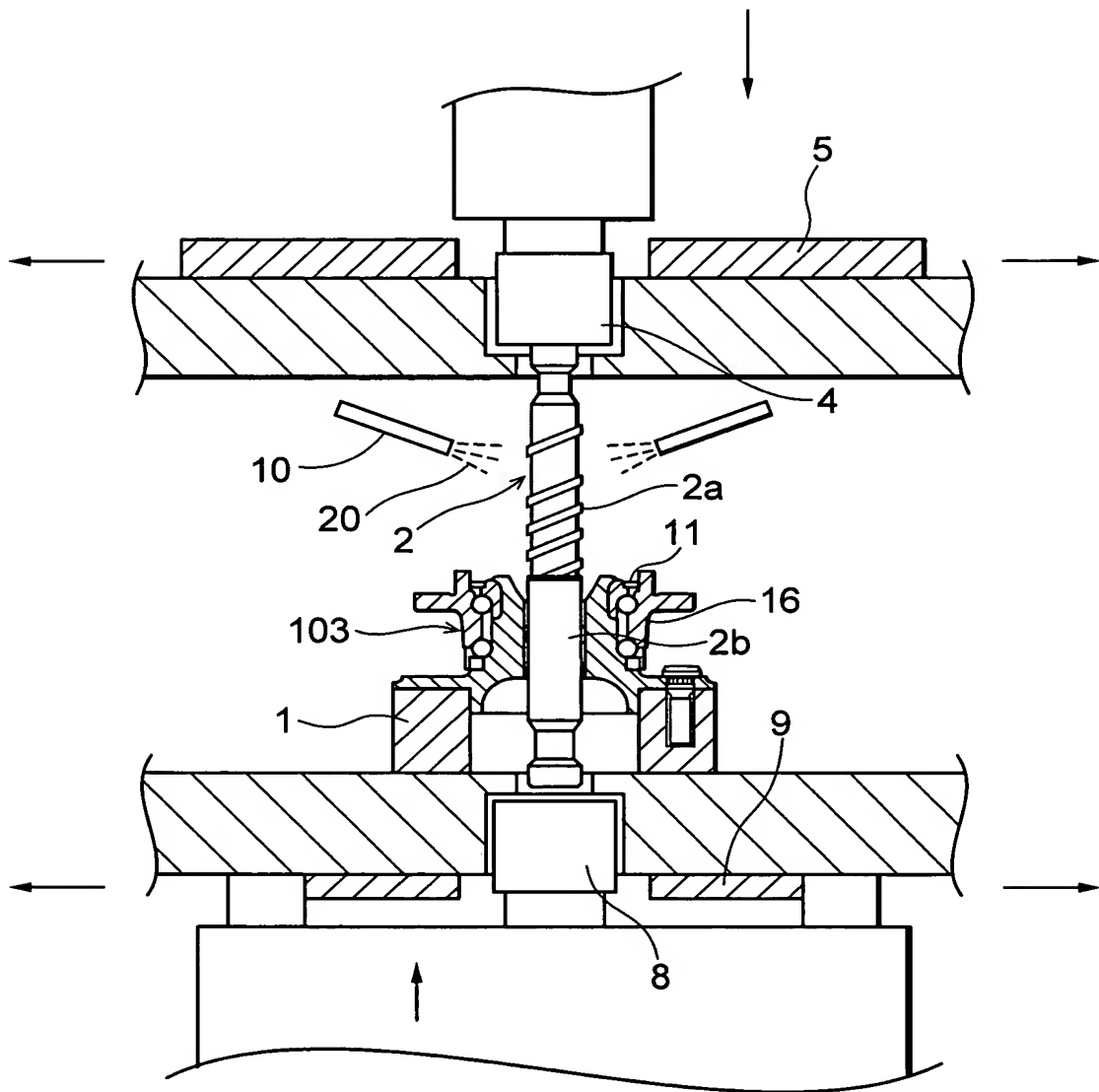


FIG. 6



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FIG. 7

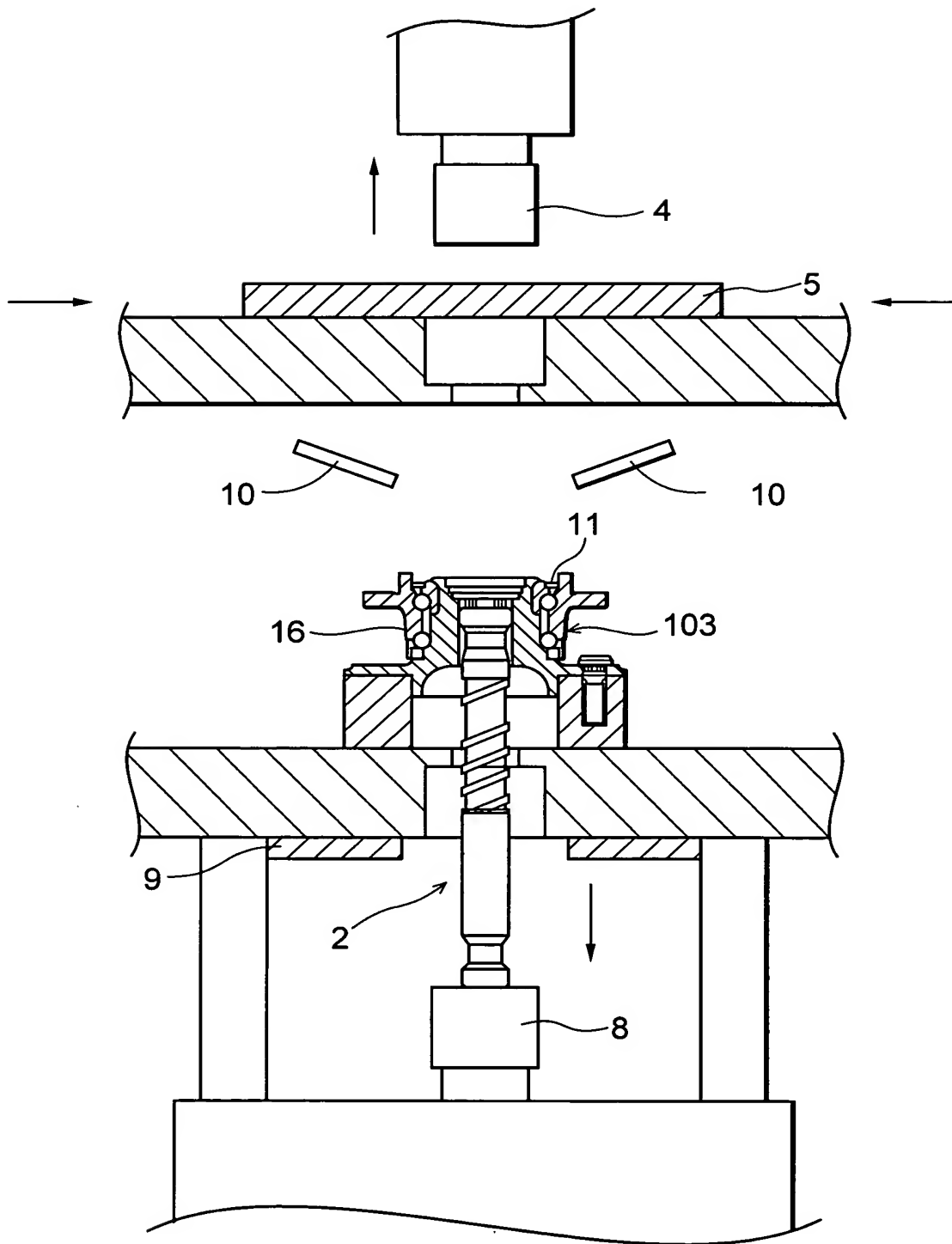


FIG. 9A

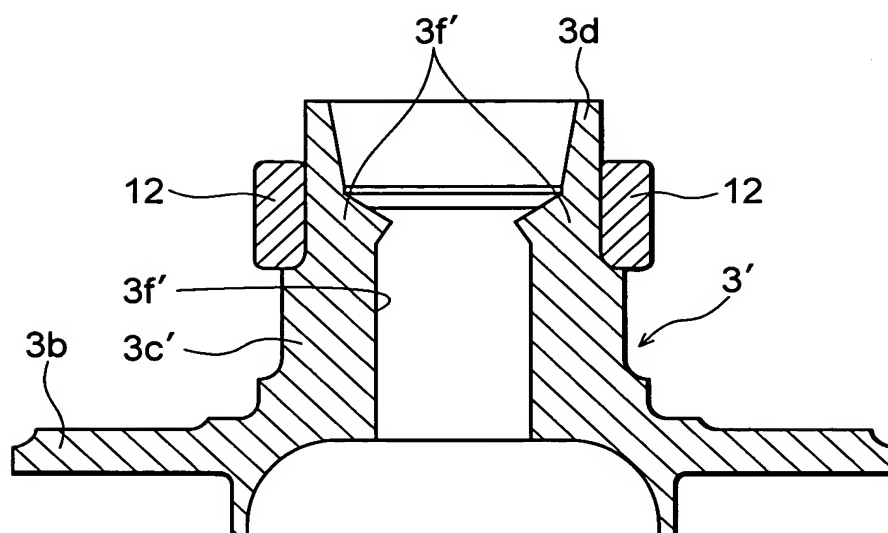
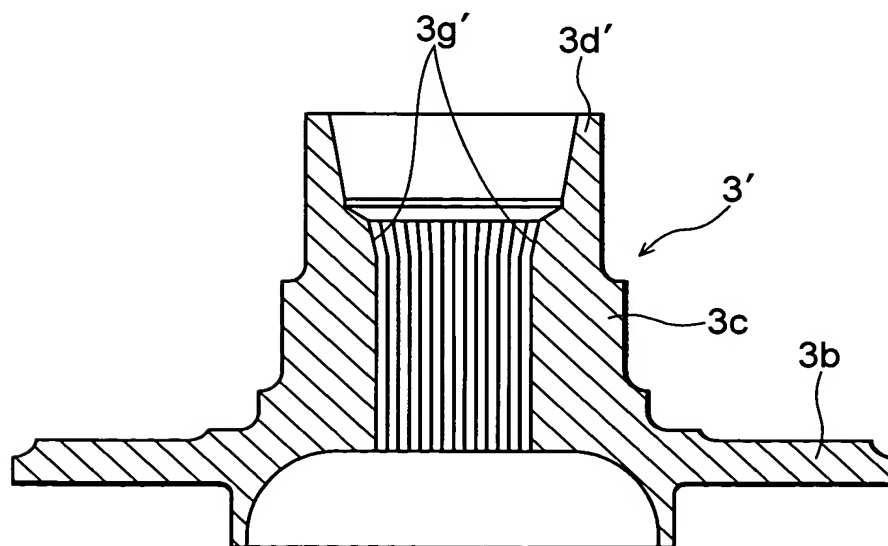


FIG. 9B



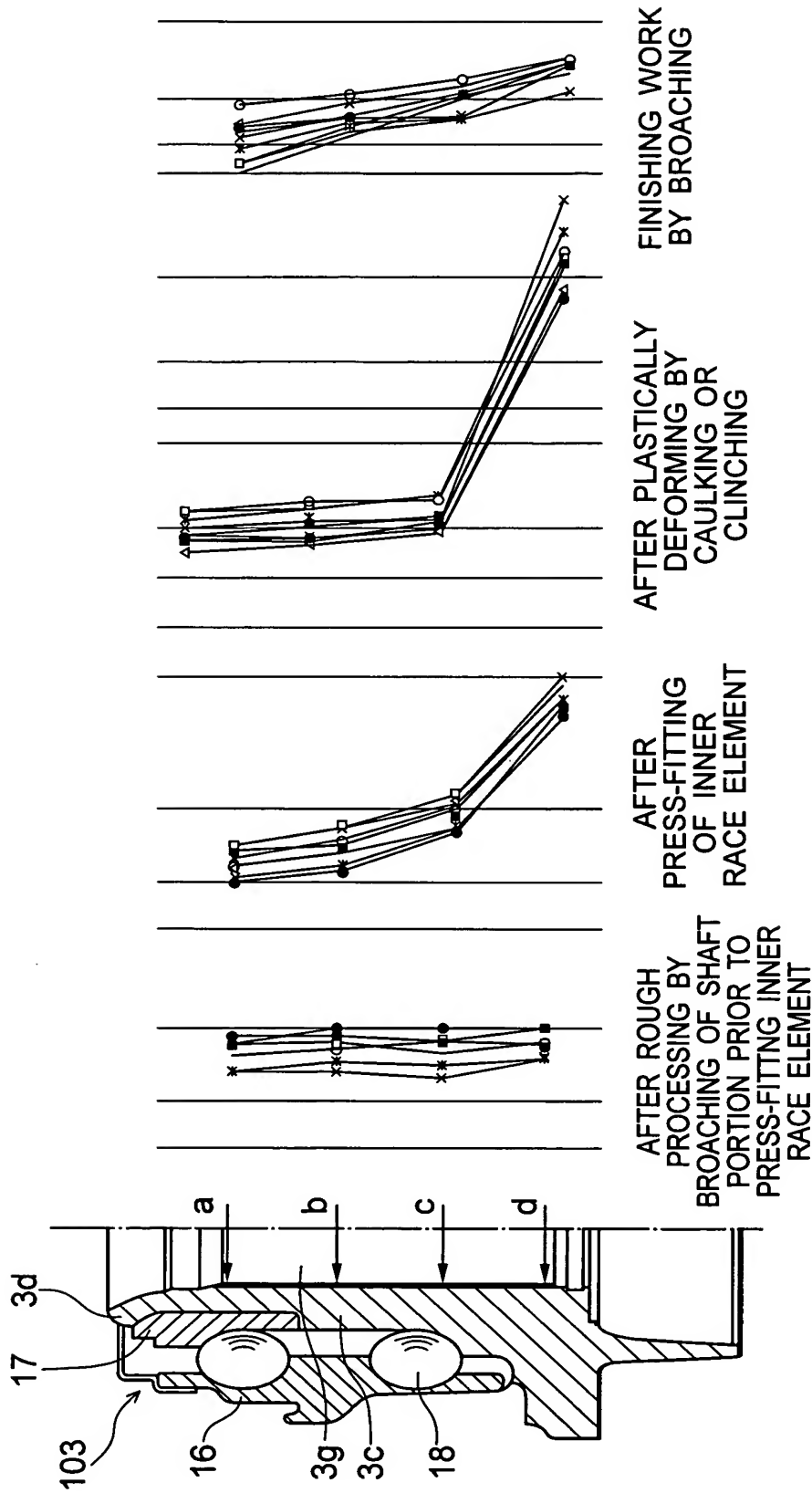


FIG.10A FIG.10B FIG.10C FIG.10D FIG.10E

Diagram illustrating a cross-sectional view of a semiconductor device. The device includes a substrate 17, a first conductive layer 3c, a second conductive layer 3d, and a third conductive layer 3e. A distance X is indicated between two vertical lines.